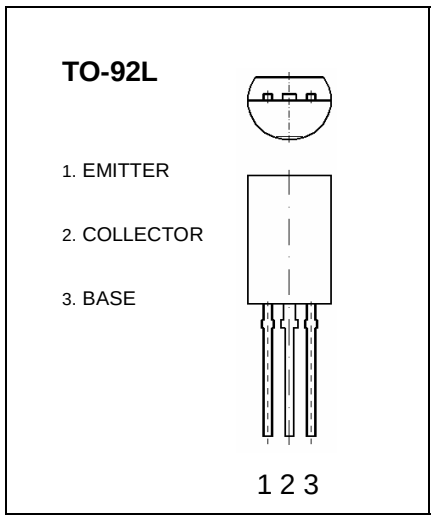
Transys Electronics LIMITED

TO-92L Plastic-Encapsulated Transistors

2SB562 TRANSISTOR (PNP)



FEATURES

Power dissipation

P_{CM}: 900 mW (Tamb=25℃)

Collector current

I_{CM}: -1 A

Collector-base voltage

$V_{(BR)CBO}$: -25 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-10μA, I_E=0	-25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=-1mA, I_B=0	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-20V, I_E=0			-1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V, I_C=0			-1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-2V, I_C=-0.5A	85		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-0.8A, I_B=-0.08A			-0.5	V
Base-emitter voltage	V_{BE}	V_{CE}=-2V, I_C=-0.5A			-1	V
Transition frequency	f_T	V_{CE}=-2V, I_C=-0.5A		350		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		38		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	B	C
Range	85-170	120-240